

Silicon PNP Power Transistors

2SB1640

DESCRIPTION

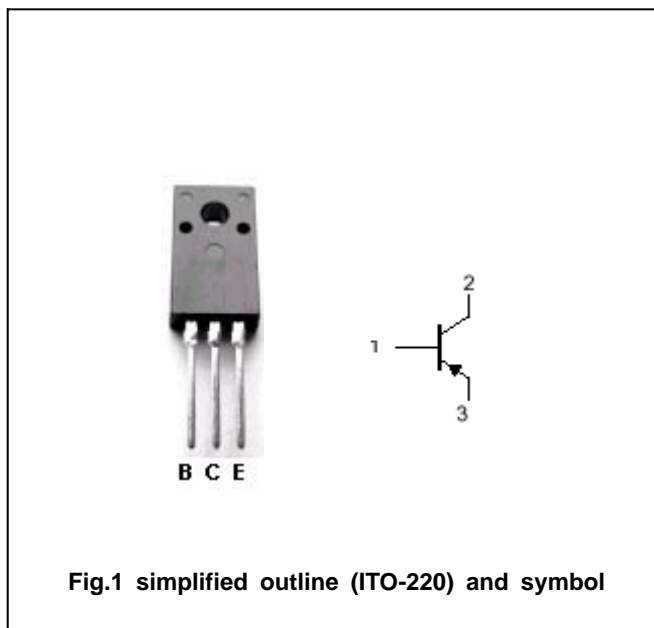
- With ITO-220 package
- Low collector saturation voltage
- Complement to type 2SD2525

APPLICATIONS

- Audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-3	A
I _B	Base current		-0.5	A
P _C	Collector power dissipation	T _C =25	1.8	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A		-1.0	-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-0.5A ; V _{CE} =-5V		-0.75	-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V ; I _E =0			-10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-7V ; I _C =0			-10	μ A
h _{FE-1}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	100		320	
h _{FE-2}	DC current gain	I _C =-2A ; V _{CE} =-5V	15			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-5V		9		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V;f=1MHz		50		pF

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PACKAGE OUTLINE

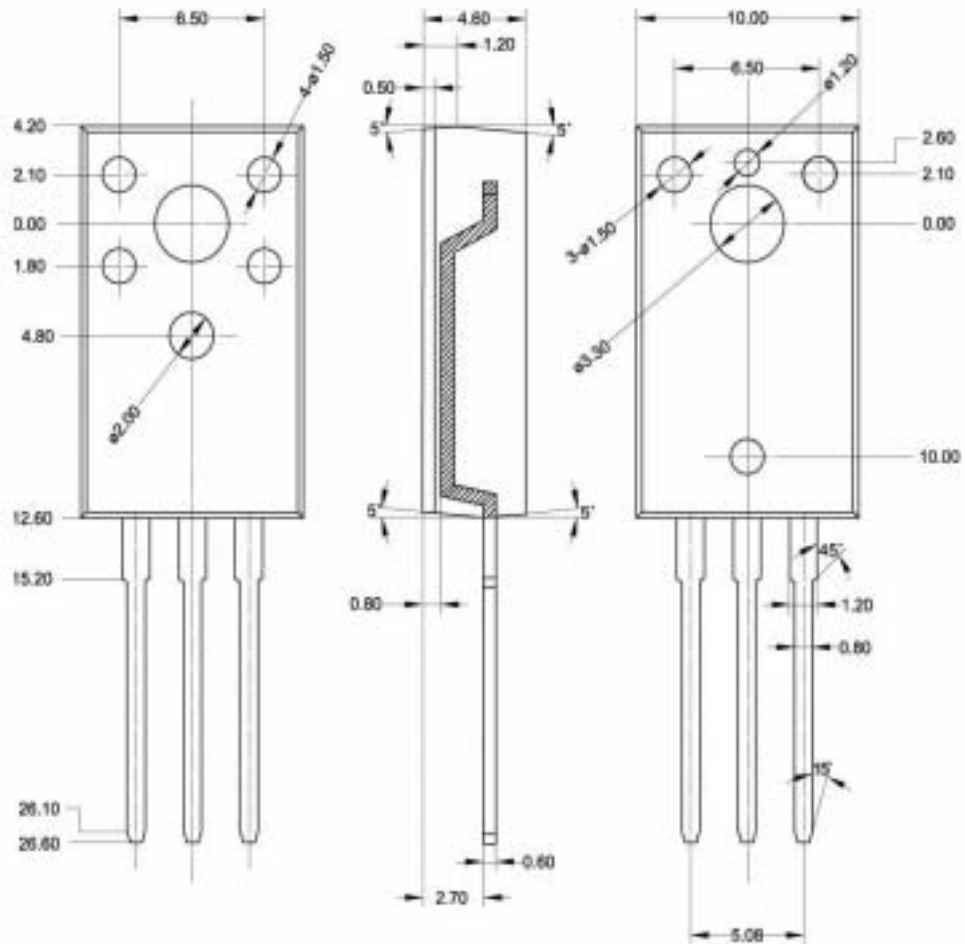


Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)